



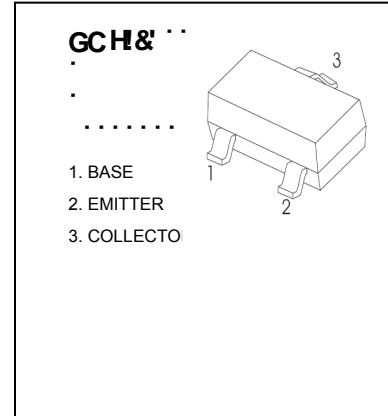
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2N2222A

9018, 2N2222A TRANSISTOR (NPN)

Features

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary types: BC807 (PNP)



Electrical Characteristics (TA = 25°C)

Symbol	Parameter	Typical Value	Unit
$V_{CE(sat)}$	Collector-Base Voltage	50	V
$V_{CE(sat)}$	Collector-Emitter Voltage	45	V
$V_{BE(sat)}$	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.5	A
P_D	Collector Power Dissipation	0.3	W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

Electrical Characteristics (TA = 25°C)

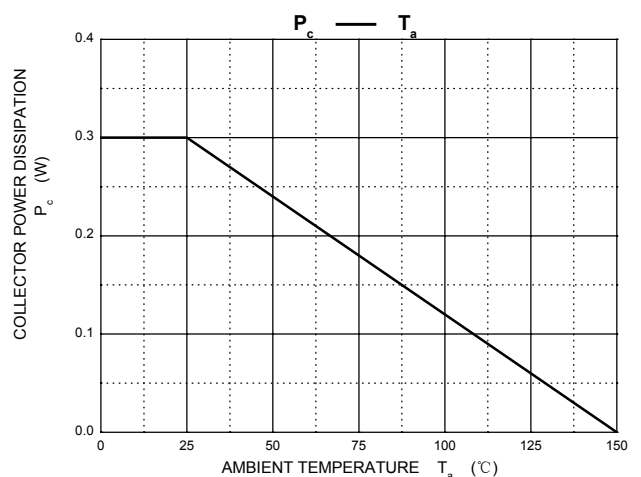
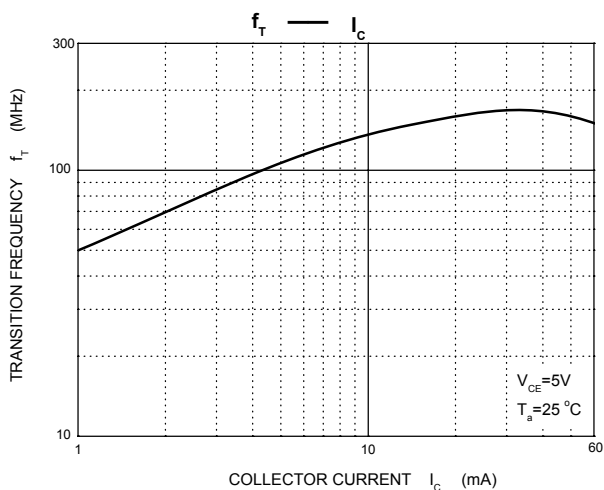
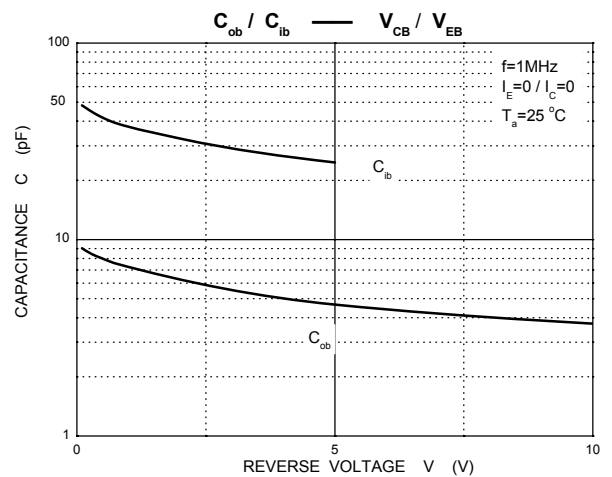
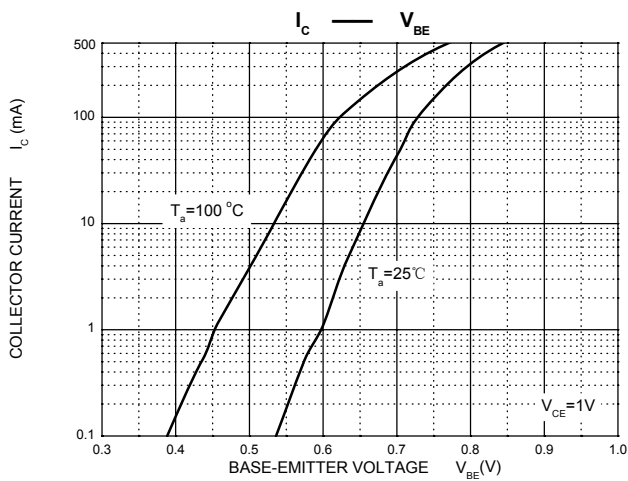
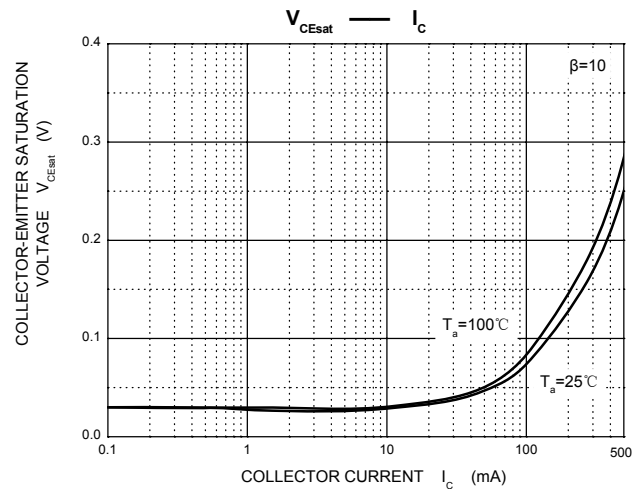
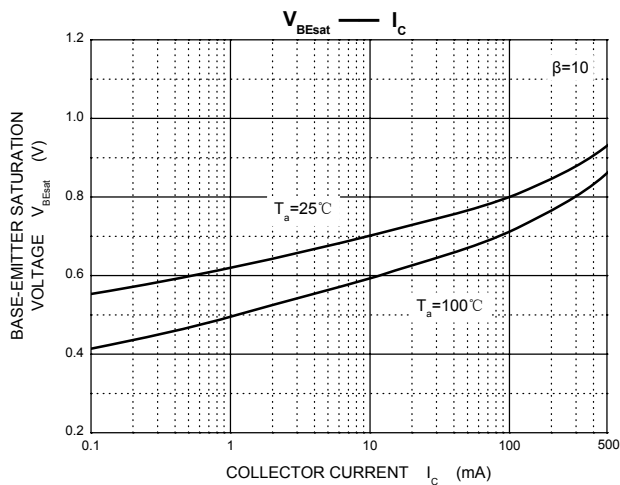
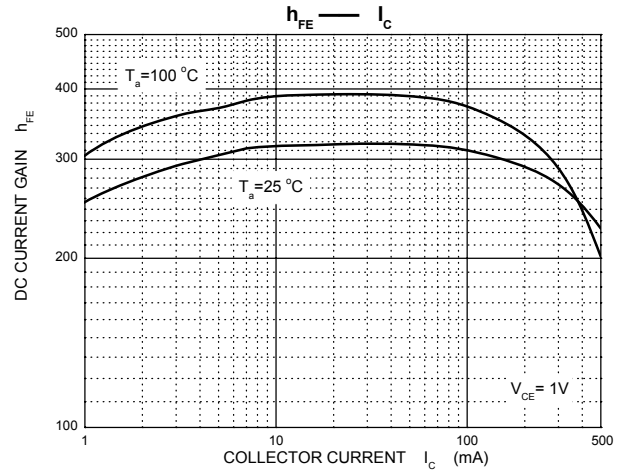
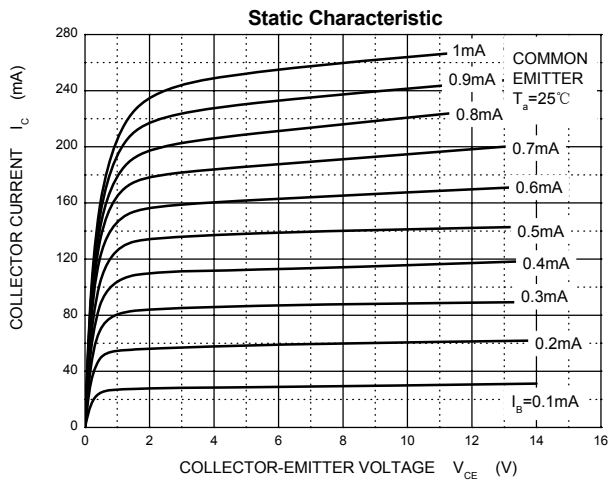
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{CE(sat)}$	Collector-Base Voltage	$I_C = 10\mu A, I_E = 0$	50			V
$V_{CE(sat)}$	Collector-Emitter Voltage	$I_C = 10mA, I_B = 0$	45			V
$V_{BE(sat)}$	Emitter-Base Voltage	$I_E = 1\mu A, I_C = 0$	5			V
I_{CBO}	Collector Current	$V_{CB} = 45V, I_E = 0$			0.1	μA
I_{EBO}	Emitter Current	$V_{EB} = 4V, I_C = 0$			0.1	μA
$h_{FE(1)}$	DC Current Gain	$V_{CE} = 1V, I_C = 100mA$	100		600	
		$V_{CE} = 1V, I_C = 500mA$	40			
$V_{CE(sat)}$	Collector-Emitter Voltage	$I_C = 500mA, I_B = 50mA$			0.7	V
$V_{BE(sat)}$	Emitter-Base Voltage	$I_C = 500mA, I_B = 50mA$			1.2	V
V_{BE}	Emitter-Base Voltage	$V_{CE} = 1V, I_C = 500mA$			1.2	V
C_{ob}	Output Capacitance	$V_{CB} = 10V, f = 1MHz$		10		pF
f_T	Transition Frequency	$V_{CE} = 5V, I_C = 10mA, f = 100MHz$	100			MHz

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta(j-c)}$ <td>Junction-Collector Thermal Resistance <td>67</td> <td>°C/W</td> </td>	Junction-Collector Thermal Resistance <td>67</td> <td>°C/W</td>	67	°C/W
$R_{\theta(j-e)}$ <td>Junction-Emitter Thermal Resistance <td>67</td> <td>°C/W</td> </td>	Junction-Emitter Thermal Resistance <td>67</td> <td>°C/W</td>	67	°C/W
$R_{\theta(j-a)}$ <td>Junction-Ambient Thermal Resistance <td>67</td> <td>°C/W</td> </td>	Junction-Ambient Thermal Resistance <td>67</td> <td>°C/W</td>	67	°C/W

Typical Characteristics

BC817



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